ELECTRONICS, INC.
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NTE2654 (NPN) & NTE2664 (PNP)
Silicon Complementary Transistors
Audio Power Amp Output

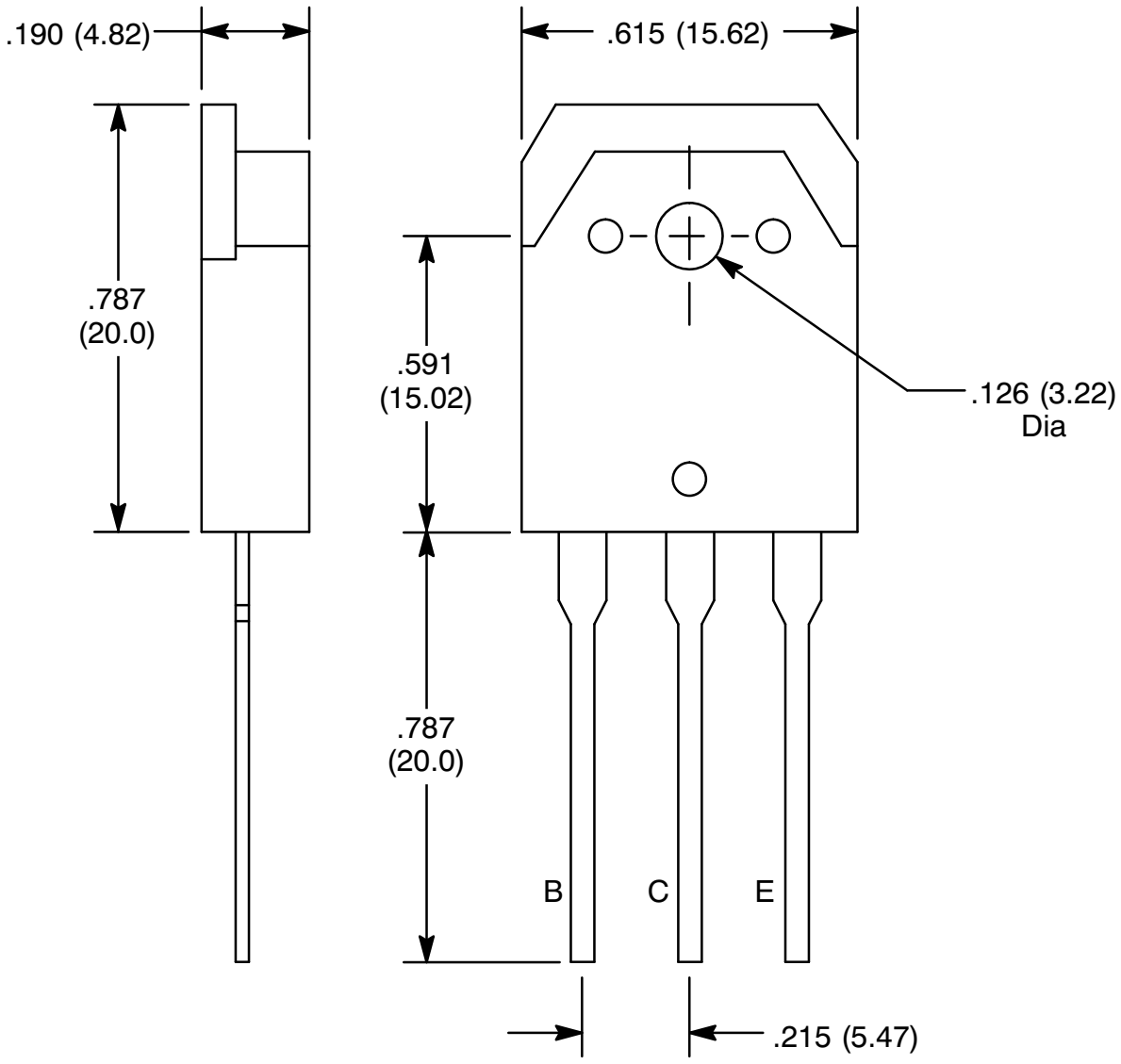
Features:
- High Collector Breakdown Voltage
- Suitable for use in 80W High Fidelity Audio Amplifier Output Stage

Absolute Maximum Ratings: (T_C = +25°C unles otherwise specified)

Collector–Base Voltage, V_{CBO} 230V
Collector–Emitter Voltage, V_{CEO} 230V
Emitter–Base Voltage, V_{EBO} 5V
Collector Current, I_C 15A
Base Current, I_B 1.5A
Collector Power Dissipation (T_C = +25°C), P_C 130W
Operating Junction Temperature, T_J . . . . . +150°C
Storage Temperature Range, T_{stg} . . . . . –55° to +150°C

Electrical Characteristics: (T_C = +25°C unles otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut–Off Current	I_{CBO}	V_{CB} = 230V, I = 0	–	–	5.0	μA
Emitter Cut–Off Current	I_{EBO}	V_{EB} = 5V, I_C = 0	–	–	5.0	μA
Collector–Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C = 50mA, I_B = 0	230	–	–	V
DC Current Gain NTE2654	h_{FE}	V_{CE} = 5V, I_C = 1A	80	–	160	
NTE2664			55	–	160	
Both Devices		V_{CE} = 5V, I_C = 7A	35	60	–	
Collector–Emitter Saturation Voltage NTE2654	$V_{CE(sat)}$	I_C = 8A, I_B = 0.8A	–	0.4	3.0	V
NTE2664			–	1.5	3.0	V
Base–Emitter Voltage	V_{BE}	V_{CE} = 5V, I_C = 7A	–	1.0	1.5	V
Transition Frequency	f_T	V_{CE} = 5V, I_C = 1A	–	30	–	MHz
Collector Output Capacitance NTE2654	C_{ob}	V_{CB} = 10V, I_E = 0, f = 1MHz	–	200	–	pF
NTE2664			–	360	–	pF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